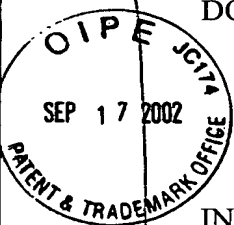


DOCKET NO.: 199143US2SRD



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

~~SHOJI OTAKA, ET AL.~~ : EXAMINER: MOTTOLA, S.

~~SERIAL NO: 09/696,972~~ :

~~FILED: OCTOBER 27, 2000~~ : GROUP ART UNIT: 2817

~~FOR: VARIABLE GAIN CIRCUIT~~ :

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated June 17, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION

Page 14, beginning at line 8, please replace the paragraph with the following:

A' The second operation is performed to correct the gain deviation due to the transition of the operation region of each MOSFET from a strong inversion region to a weak inversion region. FIG. 1C is a graph showing this correction. Note that the second correction is not required when FETs having no inverted layers, e.g., J-FETs (Junction Field-Effect Transistors) or MESFETs (Schottky junction field effect transistors), are used. By performing the corrections shown in FIGS. 1B and 1C, a linear-in-dB characteristic can be obtained even if MOSFETs are used. FIG. 1D shows this characteristic.

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